UNR31A4

Silicon PNP epitaxial planar type

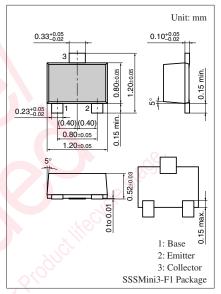
For digital circuits

Features

- Suitable for high-density mounting and downsizing of the equipment
- Contribute to low power consumption

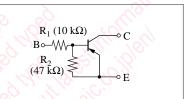
Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-50	V	
Collector-emitter voltage (Base open)	V _{CEO}	-50	V	
Collector current	I _C	-80	mA	
Total power dissipation	P _T	100	mW	
Junction temperature	Tj	125	°C	
Storage temperature	T _{stg}	-55 to +125	°C	



Marking Symbol: CK

Internal Connection



Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu A, I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = -50 \text{ V}, I_B = 0$			- 0.5	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = -6 V, I_C = 0$			- 0.2	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	80			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.3 \text{ mA}$			- 0.25	V
Output voltage high level	V _{OH}	$V_{CC} = -5 \text{ V}, \text{V}_{B} = -0.5 \text{V}, \text{R}_{L} = 1 \text{k} \Omega$	-4.9			V
Output voltage low level	V _{OL}	$V_{CC} = -5 \text{ V}, \text{ V}_{B} = -2.5 \text{ V}, \text{ R}_{L} = 1 \text{ k}\Omega$			- 0.2	V
Input resistance	R ₁		-30%	10	+30%	kΩ
Resistance ratio	R ₁ / R ₂		0.17	0.21	0.25	_
Transition frequency	f _T	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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120

100

80

60

40

20

0 L 0

300

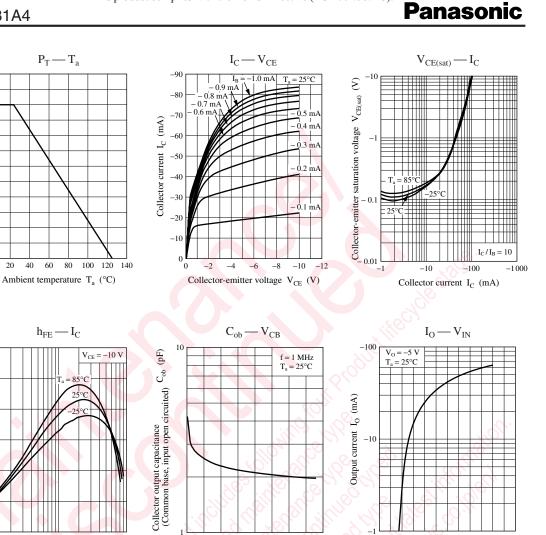
50

0

-1

20 40 60 80

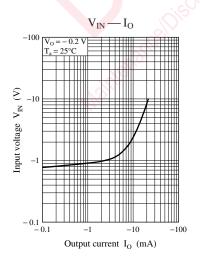
Total power dissipation P_{T} (mW)



-2 -3 -4 -5 -6

Input voltage V_{IN} (V)

0 -1



-10

Collector current I_C (mA)

-100

0

-20

Collector-base voltage V_{CB} (V)

-30

-40

-10

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